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3mm Dia., Four-Element Segmented InGaAs Photodiode



#17-078, 3mm Dia., Four-Element Segmented InGaAs Photodiode

Stock **#17-078** [CONTACT US](#)

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+

A\$984⁰⁰

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Volume Pricing	
Qty 1-4	A\$984.00 each
Qty 5-9	A\$872.00 each
Qty 10-24	A\$811.20 each
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Product Downloads

General	
24 (typical)	Rise/ Fall Time @ V _R =5V (ns):
Physical & Mechanical Properties	
3 Dia.	Size of Active Area (mm):
0.045	Element Gap (mm):

Electrical

	Responsivity @ 1310nm (AW): 0.85 minimum / 0.9 typical
	Responsivity @ 1550nm (AW): 0.9 minimum / 0.95 typical
	Capacitance @ V_R=5V (pF): 225
	Noise Equivalent Power NEP (W/ Hz^{1/2}): 2.50 x 10 ⁻¹⁴ @ 1550nm
	Maximum Reverse Voltage (V): 10
	Dark Current @ V_R=5V (nA): Maximum: 100 Typical: 2.0

Hardware & Interface Connectivity

	Connector: TO-8
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Environmental & Durability Factors

	Operating Temperature (°C): -40 to +75
	Storage Temperature (°C): -55 to +125

Regulatory Compliance

	Certificate of Conformance: View
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Product Details

- Four Individual Active Area Elements
- High Response Uniformity and Low Crosstalk
- Ideal for Position Detection and Beam Alignment
- [Segmented Silicon Photodiodes](#) and [InGaAs Photodiodes](#) Also Available

Segmented InGaAs Photodiodes feature large active areas divided into four individual elements. The four elements of these photodiodes have high response uniformity and low crosstalk, enabling their use in accurate nulling or centering applications. These photodiodes are stable over time and temperature, providing responsivity from 900 - 1700nm with excellent responsivity between 1100 - 1620nm. Segmented InGaAs Photodiodes are ideal for position detection, beam alignment, and beam profiling applications in the near-infrared spectrum. Each photodiode is packaged in an isolated TO-5 or TO-8 can with an antireflection coated window to increase throughput.

Technical Information

